

PHP18NQ11T

N-channel TrenchMOS standard level FET Rev. 02 — 10 March 2010

Product data sheet

Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

- Class-D audio amplifiers
- DC-to-DC convertors

- Inverters
- Switched-mode power supplies

1.4 Quick reference data

Table 1. **Quick reference**

Parameter	Conditions	Min	Тур	Max	Unit
drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	110	V
drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> and <u>3</u>	-	-	18	Α
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	79	W
characteristics					
gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 18 \text{ A};$ $V_{DS} = 80 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 11	-	8	-	nC
naracteristics					
drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 9 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 9 and 10	-	80	90	mΩ
	drain-source voltage drain current total power dissipation characteristics gate-drain charge paracteristics drain-source	drain-source voltage $T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$ drain current $T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V};$ see Figure 1 and 3 total power dissipation $T_{mb} = 25 ^{\circ}\text{C}; \text{see Figure 2}$ characteristics gate-drain charge $V_{GS} = 10 \text{V}; I_D = 18 \text{A};$ $V_{DS} = 80 \text{V}; T_j = 25 ^{\circ}\text{C};$ see Figure 11 paracteristics drain-source $V_{GS} = 10 \text{V}; I_D = 9 \text{A};$ $V_{DS} = 10 \text{V}; I_D = 9 \text{A};$	drain-source voltage $T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$ - drain current $T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V};$ - see Figure 1 and 3 total power dissipation $T_{mb} = 25 ^{\circ}\text{C}; \text{see Figure 2}$ - dissipation $T_{mb} = 25 ^{\circ}\text{C}; \text{see Figure 2}$ - characteristics gate-drain charge $V_{GS} = 10 \text{V}; I_D = 18 \text{A};$ - $V_{DS} = 80 \text{V}; T_j = 25 ^{\circ}\text{C};$ see Figure 11 maracteristics drain-source $V_{GS} = 10 \text{V}; I_D = 9 \text{A};$ - on-state resistance $V_{GS} = 10 \text{V}; I_D = 9 \text{A};$ - $V_{DS} = 25 ^{\circ}\text{C};$	drain-source voltage $T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$ drain current $T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 V;$ see Figure 1 and 3 total power dissipation $T_{mb} = 25 ^{\circ}\text{C}; \text{see Figure 2}$	drain-source voltage $T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$ 110 drain current $T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V};$ 18 total power dissipation $T_{mb} = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 2}}{\text{Institute of the constraints}}$ - 79 dissipation $T_{mb} = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 2}}{\text{Institute of the constraints}}$ - 8 - 79 dissipation $T_{mb} = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 2}}{\text{Institute of the constraints}}$ - 8 - 8 - 8 - 90 drain-source $T_{max} = 10 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 11}}{\text{Institute of the constraints}}$ - 80 90 on-state resistance $T_j = 25 ^{\circ}\text{C};$



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PHP18NQ11T	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$	-	110	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	110	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	13	Α
		$V_{GS} = 10 \text{ V}$; $T_{mb} = 25 \text{ °C}$; see <u>Figure 1</u> and <u>3</u>	-	18	Α
I_{DM}	peak drain current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$; see <u>Figure 3</u>	-	72	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	79	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-dr	ain diode				
Is	source current	$T_{mb} = 25 ^{\circ}C$	-	18	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	72	Α
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 11 A; $V_{sup} \le$ 25 V; unclamped; t_p = 0.1 ms; R_{GS} = 50 Ω	-	70	mJ

PHP18NQ11T_2

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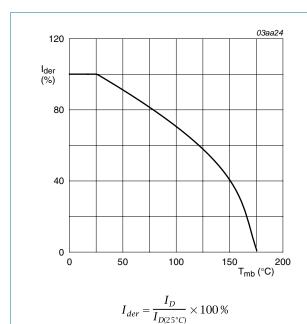


Fig 1. Normalized continuous drain current as a function of mounting base temperature

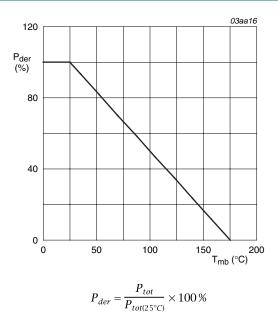
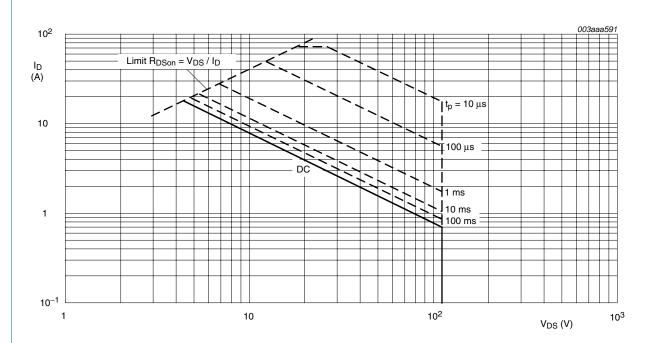


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25$ °C; I_{DM} is single pulse; $V_{GS} = 10V$

Fig 3. Safe operating area: continuous and peak currents as a function of drain-source voltage

Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.9	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

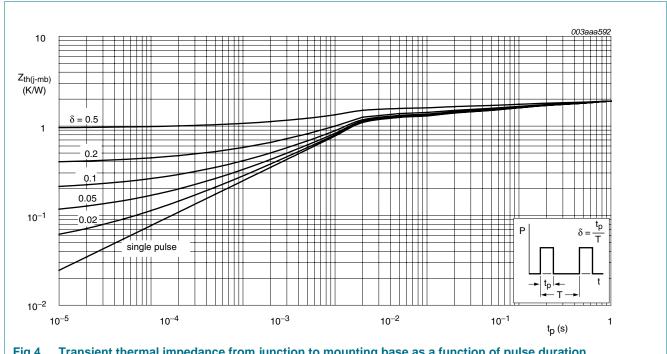


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS} drain-source		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	98	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	110	-	-	V
V _{GS(th)} gate-source th voltage	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see <u>Figure 8</u>	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 8	2	3	4	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 8	-	-	4.4	V
I _{DSS}	drain leakage current	$V_{DS} = 110 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 110 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
R _{DSon} drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 9 \text{ A}; T_j = 175 °C;$ see Figure 9 and 10	-	-	243	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 9 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 9 and 10	-	80	90	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 18 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$	-	21	-	nC
Q _{GS}	gate-source charge	$T_j = 25$ °C; see <u>Figure 11</u>	-	4	-	nC
Q_{GD}	gate-drain charge		-	8	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	633	-	pF
C _{oss}	output capacitance	$T_j = 25$ °C; see <u>Figure 12</u>	-	103	-	pF
C _{rss}	reverse transfer capacitance		-	61	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2.7 \Omega; V_{GS} = 10 \text{ V};$	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 °C; I_D = 18.5 A$	-	36	-	ns
t _{d(off)}	turn-off delay time		-	18	-	ns
t _f	fall time		-	12	-	ns
Source-di	rain diode					
V_{SD}	source-drain voltage	$I_S = 18 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 13	-	0.92	1.2	V
t _{rr}	reverse recovery time	$I_S = 18 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	55	-	ns
Q _r	recovered charge	$V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	135	-	nC

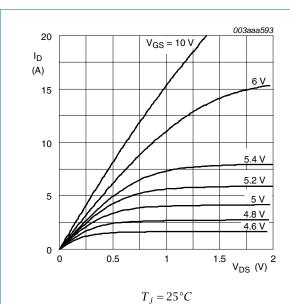
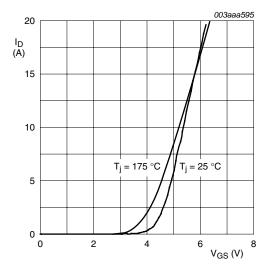


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_j = 25$ °C and 175°C; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

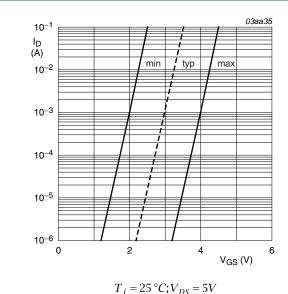
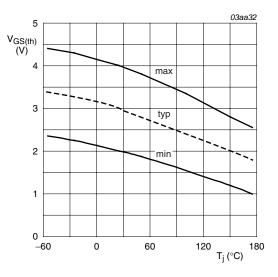


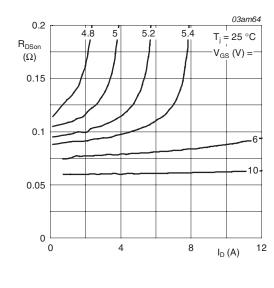
Fig 7. Sub-threshold drain current as a function of

gate-source voltage



 $I_D = 1 \, mA; V_{DS} = V_{GS}$

Fig 8. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25$ °C

Fig 9. Drain-source on-state resistance as a function of drain current; typical values

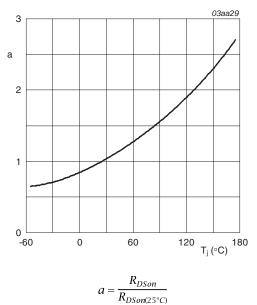
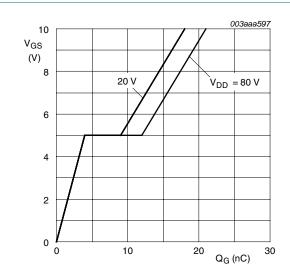


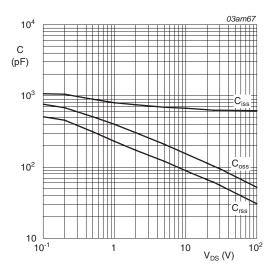
Fig 10. Normalized drain-source on-state resistance

factor as a function of junction temperature



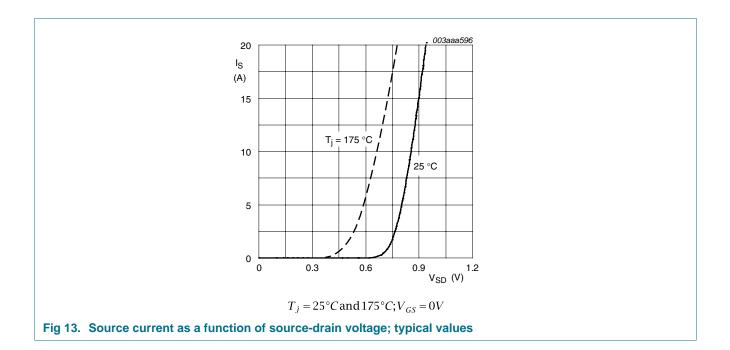
 $I_D = 3A; V_{DD} = 20V \text{ and } 80V$

Fig 11. Gate-source voltage as a function of gate charge; typical values



 $V_{\it GS}=0V; f=1MHz$ Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical

values



Package outline

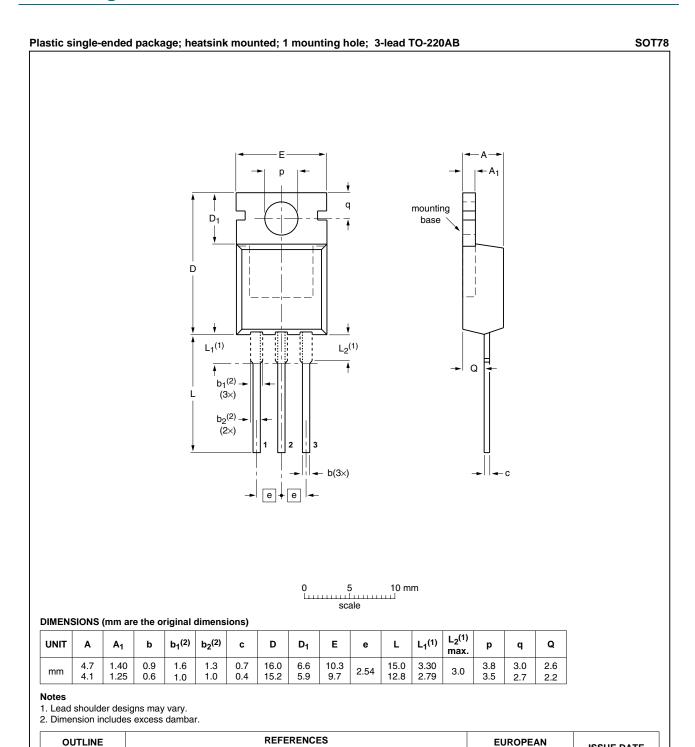


Fig 14. Package outline SOT78 (TO-220AB)

IEC

JEDEC

3-lead TO-220AB

JEITA

SC-46

ISSUE DATE

08-04-23

08-06-13

PROJECTION

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SOT78

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP18NQ11T_2	20100310	Product data sheet	-	PHP18NQ11T-01
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 			
	 Legal texts 	have been adapted to the	new company name whe	re appropriate.
PHP18NQ11T-01 (9397 750 12305)	20031113	Product data	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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